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Poster Presentation

## [AMDp1]Oxide TFTs

Thu. Nov 28, 2019 10:40 AM - 1:10 PM Main Hall (1F)

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10:40 AM - 1:10 PM

### [AMDp1-14]Effect of Mo and MoTi Serving as a Barrier Layer for Cu Source/Drain Electrodes on Performances of Amorphous Silicon and IGZO TFTs

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Keywords:Cu diffusion, Barrier layer, Electrical characteristics, TOF-SIMS

The research reveals the effect of Mo and MoTi film on the suppression of Cu diffusion for BCE structure of a-Si and a-IGZO devices during severe thermal process. Electrical characters depict that a-IGZO film is superior to a-Si for suppressing Cu diffusion, resulting from untraceable Cu signal in ToF-SIMS.